DATA SHEET WWW.DZSC.COM 74ABT126 Quad buffer (3-State)

INTEGRATED CIRCUITS

Product specification Supersedes data of 1996 Feb 26 IC23 Data Handbook

1998 Jan 16







Product specification

Quad buffer (3-State)

74ABT126

FEATURES

- Quad bus interface
- 3-State buffers
- Live insertion/extraction permitted
- Output capability: +64mA/–32mA
- Latch-up protection exceeds 500mA per JEDEC Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Power-up 3-State
- Inputs are disabled during 3-State mode

QUICK REFERENCE DATA

DESCRIPTION

The 74ABT126 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT126 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables (OE0, OE1, OE2, OE3), each controlling one of the 3-State outputs.

| SYMBOL | PARAMETER | CONDITIONS T _{amb} = 25°C; GND = 0V | TYPICAL | UNIT |
|--------------------------------------|-------------------------------|---|---------|------|
| t _{PLH} t _{PHL} | Propagation delay An to Yn | $C_L = 50 pF; V_{CC} = 5V$ | 2.9 | ns |
| C _{IN} | Input capacitance | $V_I = 0V \text{ or } V_{CC}$ | 4 | pF |
| C _{OUT} | Output capacitance | Outputs disabled; V _O = 0V or V _{CC} | 7 | pF |
| I _{CCZ} | Total supply current | Outputs disabled; V _{CC} = 5.5V | 65 | μΑ |

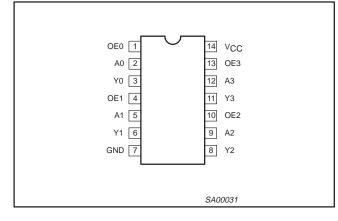
ORDERING INFORMATION

| PACKAGES | TEMPERATURE RANGE | OUTSIDE NORTH AMERICA | NORTH AMERICA | DWG NUMBER |
|-----------------------------|-------------------|-----------------------|---------------|------------|
| 14-Pin Plastic DIP | -40°C to +85°C | 74ABT126 N | 74ABT126 N | SOT27-1 |
| 14-Pin plastic SO | -40°C to +85°C | 74ABT126 D | 74ABT126 D | SOT108-1 |
| 14-Pin Plastic SSOP Type II | -40°C to +85°C | 74ABT126 DB | 74ABT126 DB | SOT337-1 |
| 14-Pin Plastic TSSOP Type I | -40°C to +85°C | 74ABT126 PW | 74ABT126PW DH | SOT402-1 |

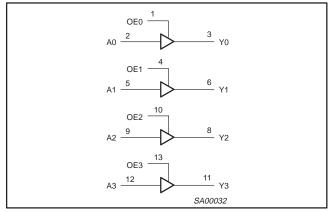
PIN DESCRIPTION

| PIN NUMBER | SYMBOL | NAME AND FUNCTION |
|--------------|-----------------|-------------------------|
| 2, 5, 9, 12 | A0 – A3 | Data inputs |
| 3, 6, 8, 11 | Y0 – Y3 | Data outputs |
| 1, 4, 10, 13 | OE0 – OE3 | Output enable inputs |
| 7 | GND | Ground (0V) |
| 14 | V _{CC} | Positive supply voltage |

PIN CONFIGURATION



LOGIC SYMBOL



74ABT126

OUTPUTS

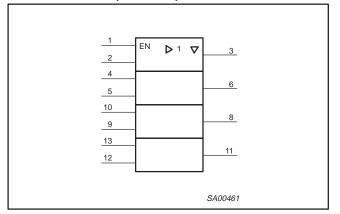
Yn

L

Н

Ζ

LOGIC SYMBOL (IEEE/IEC)



ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL PARAMETER CONDITIONS RATING UNIT DC supply voltage -0.5 to +7.0 V Vcc DC input diode current -18 I_{IK} $V_{I} < 0$ mΑ Vı DC input voltage³ -1.2 to +7.0 V DC output diode current $V_{\rm O} < 0$ -50 mΑ I_{OK} V Vout DC output voltage³ output in Off or High state -0.5 to +5.5 DC output current output in Low state 128 mΑ I_{OUT} T_{stg} Storage temperature range -65 to 150 °C

FUNCTION TABLE

OEn

Н

Н

L

H = High voltage level

L = Low voltage level

Z = High impedance "off" state

= Don't care

Х

INPUTS

An

L

Н

Х

NOTES:

Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the 1. device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction 2. temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

| SYMBOL | PARAMETER | LIM | ITS | UNIT |
|------------------|--------------------------------------|-----|-----------------|------|
| STWBOL | FARAMEIER | Min | UNIT | |
| V _{CC} | DC supply voltage | 4.5 | 5.5 | V |
| VI | Input voltage | 0 | V _{CC} | V |
| V _{IH} | High-level input voltage | 2.0 | | V |
| V _{IL} | Low-level Input voltage | | 0.8 | V |
| I _{ОН} | High-level output current | | -32 | mA |
| I _{OL} | Low-level output current | | 64 | mA |
| Δt/Δv | Input transition rise or fall rate | 0 | 10 | ns/V |
| T _{amb} | Operating free-air temperature range | -40 | +85 | °C |

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| | | | | | LIMITS | | | |
|----------------------------------|--|--|--------------------------|-------|--------|--------------------------------------|------|----|
| SYMBOL | PARAMETER | TEST CONDITIONS | T _{amb} = +25°C | | | T _{amb} = −40°C to +85°C | | |
| | | | Min | Тур | Max | Min | Max | 1 |
| V _{IK} | Input clamp voltage | $V_{CC} = 4.5V; I_{IK} = -18mA$ | | -0.9 | -1.2 | | -1.2 | V |
| | | V_{CC} = 4.5V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH} | 2.5 | 2.9 | | 2.5 | | V |
| V _{OH} | High-level output voltage | V_{CC} = 5.0V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH} | 3.0 | 3.4 | | 3.0 | | V |
| | | V_{CC} = 4.5V; I_{OH} = –32mA; V_{I} = V_{IL} or V_{IH} | 2.0 | 2.4 | | 2.0 | | V |
| V _{OL} | Low-level output voltage | V_{CC} = 4.5V; I_{OL} = 64mA; V_{I} = V_{IL} or V_{IH} | | 0.35 | 0.55 | | 0.55 | V |
| I _I | Input leakage current | V_{CC} = 5.5V; V_I = GND or 5.5V | | ±0.01 | ±1.0 | | ±1.0 | μΑ |
| I _{OFF} | Power-off leakage current | V_{CC} = 0.0V; V_O or $V_I \le 4.5V$ | | ±5.0 | ±100 | | ±100 | μA |
| I _{PU} /I _{PD} | Power-up/down 3-State output current ³ | $V_{CC} = 2.1V; V_O = 0.5V; V_I GND \text{ or } V_{CC};$ $V_{OE} = Don't \text{ care}$ | | ±5.0 | ±50 | | ±50 | μA |
| I _{OZH} | 3-State output High current | V_{CC} = 5.5V; V_{O} = 2.7V; V_{I} = V_{IL} or V_{IH} | | 1.0 | 50 | | 50 | μA |
| I _{OZL} | 3-State output Low current | V_{CC} = 5.5V; V_{O} = 0.5V; V_{I} = V_{IL} or V_{IH} | | -1.0 | -50 | | -50 | μA |
| I _{CEX} | Output High leakage current | V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND or V_{CC} | | 5.0 | 50 | | 50 | μA |
| Ι _Ο | Output current ¹ | $V_{CC} = 5.5V; V_{O} = 2.5V$ | -50 | -100 | -180 | -50 | -180 | mA |
| I _{CCH} | | V_{CC} = 5.5V; Outputs High, V_{I} = GND or V_{CC} | | 65 | 250 | | 250 | μA |
| I _{CCL} | Quiescent supply current | V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC} | | 12 | 15 | | 15 | mA |
| I _{CCZ} | | V_{CC} = 5.5V; Outputs 3–State; V _I = GND or V _{CC} | | 65 | 250 | | 250 | μA |
| | | Outputs enabled, one data input at 3.4V, other inputs at V _{CC} or GND; $V_{CC} = 5.5V$ | | 0.5 | 1.5 | | 1.5 | mA |
| ΔI_{CC} | Additional supply current per input pin ² | | | 250 | μA | | | |
| | | Outputs 3-State, one enable input at 3.4V, other inputs at V _{CC} or GND; $V_{CC} = 5.5V$ | | 0.5 | 1.5 | | 1.5 | mA |

DC ELECTRICAL CHARACTERISTICS

NOTES:

1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

2. This is the increase in supply current for each input at 3.4V. 3. This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to10msec. From V_{CC} = 2.1V to V_{CC} = 5V \pm 10%, a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

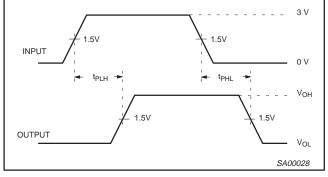
GND = 0V; $t_R = t_F$ = 2.5ns; C_L = 50pF, R_L = 500 Ω

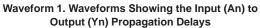
| | | | | | LIMI | ſS | | |
|--------------------------------------|--|----------|---------------------|--|------------|--|--------------------------|------|
| SYMBOL | PARAMETER | WAVEFORM | T _a V | _{mb} = +25° _{CC} = +5.0 | C V | $T_{amb} = -40^{\circ}$ $V_{CC} = +5.$ | °C to +85°C .0V ±0.5V | UNIT |
| | | | Min | Тур | Мах | Min | Мах | |
| t _{PLH} t _{PHL} | Propagation delay An to Yn | 1 | 1.0 1.0 | 2.9 3.0 | 4.2 4.3 | 1.0 1.0 | 4.4 4.6 | ns |
| t _{PZH} t _{PZL} | Output enable time to High and Low level | 2 | 1.9 1.9 | 3.2 4.4 | 5.8 5.9 | 1.9 1.9 | 6.5 6.5 | ns |
| t _{PHZ} t _{PLZ} | Output disable time from High and Low level | 2 | 1.0 1.0 | 4.2 2.9 | 5.2 4.9 | 1.0 1.0 | 5.8 5.5 | ns |

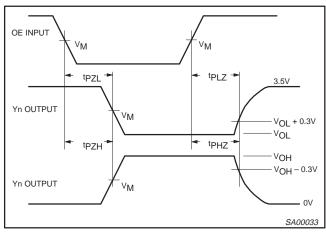
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AC WAVEFORMS

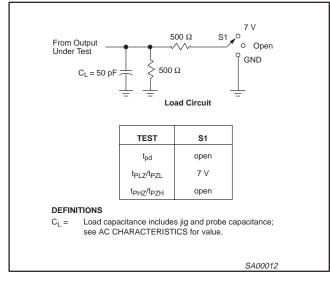
 V_{M} = 1.5V, V_{IN} = GND to 3.0V



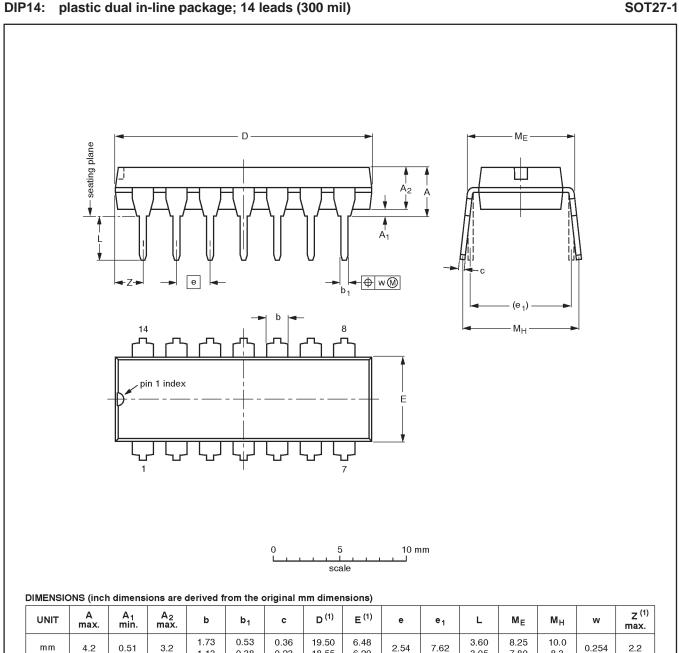




Waveform 2. Waveforms Showing the 3–State Output Enable and Disable Times



TEST CIRCUIT AND WAVEFORMS



DIP14: plastic dual in-line package; 14 leads (300 mil)

| e |
|---|
| |

inches

0.17

0.020

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

0.13

1.13

0.068

0.044

0.38

0.021

0.015

0.23

0.014

0.009

18.55

0.77

0.73

6.20

0.26

0.24

0.10

0.30

3.05

0.14

0.12

7.80

0.32

0.31

8.3

0.39

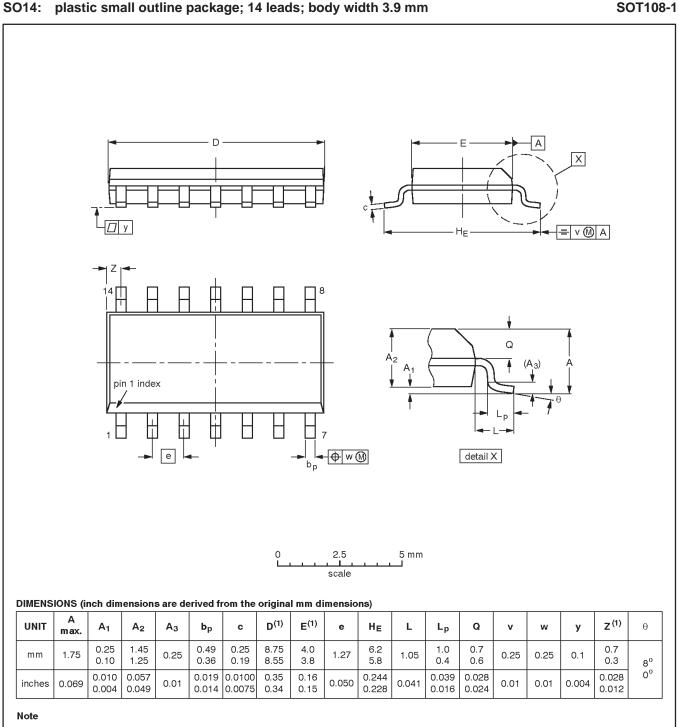
0.33

0.01

0.087

| OUTLINE | REFERENCES | | | EUROPEAN | ISSUE DATE | |
|---------|------------|----------|------|----------|------------|----------------------------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | |
| SOT27-1 | 050G04 | MO-001AA | | | | -92-11-17 95-03-11 |

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1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

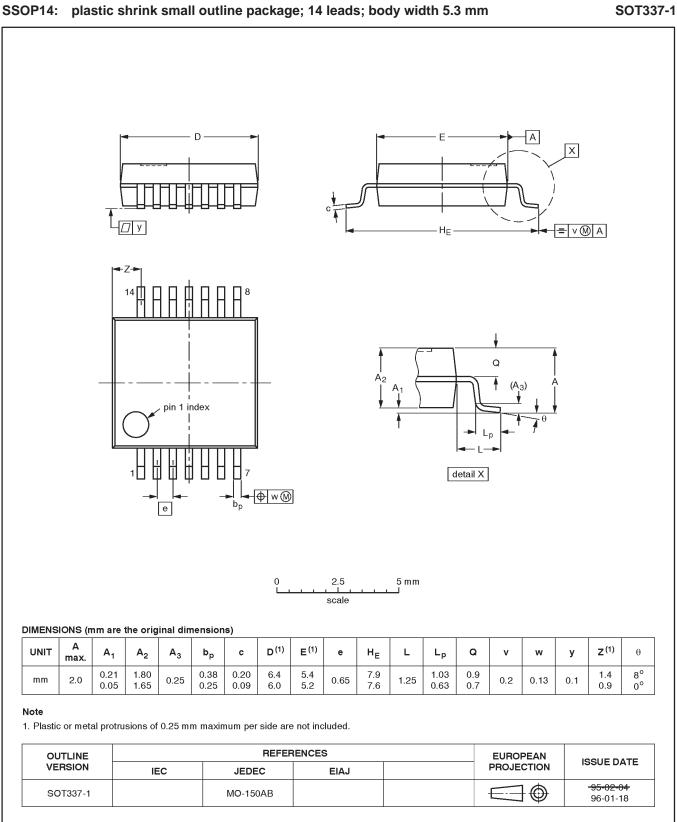
| OUTLINE | REFERENCES EUROPEAN LISS | | | | ISSUE DATE | |
|----------|--------------------------|----------|------|--|------------|----------------------------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | |
| SOT108-1 | 076E06S | MS-012AB | | | | -95-01-23 97-05-22 |
| | | | | | | |

Product specification

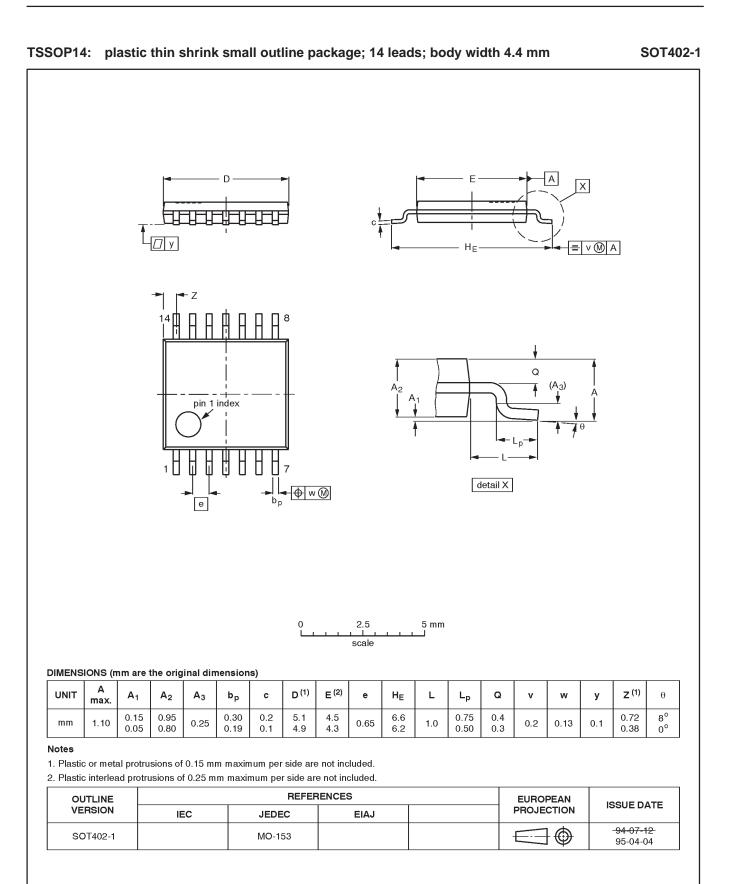
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74ADTT2

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| DEFINITIONS | | | | | |
|---------------------------|------------------------|--|--|--|--|
| Data Sheet Identification | Product Status | Definition | | | |
| Objective Specification | Formative or in Design | This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice. | | | |
| | | This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product. | | | |
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